

AMENDMENTS TO THE ABSTRACT

Please replace the abstract with the following amended abstract:

~~The present invention provides a~~ A semiconductor device is disclosed that is capable of preventing a pattern collapse phenomenon in a cell edge area in which a pattern is more fragile. The ~~inventive~~ semiconductor device ~~having~~ has a lower pattern density in an edge area than in a central area of a wafer and includes a plurality of bar-type patterns allocated at a predetermined distance in the central area of the wafer; a plurality of dummy patterns formed in the edge area; and a plurality of a connection pattern for coupling at least two of the bar-type patterns to each other, wherein the connection patterns of the plurality of dummy patterns offset or staggered with respect to each other to form a disconnected is ~~allocated in a zigzag fashion pattern.~~